the substrate surface, an 3 being severe peeling of the film from the substrate surface. The substrates of Table 2 were analyzed and it was observed that decreasing platen rotational speed results in reduced film delamination, increasing carrier head rotational speed resulting in reduced film delamination, and a greater carrier head rotational speed than platen rotational speed resulted in reduced film delamination.

Table 2: Rotational Speed Differential

Degree of peeling (0=no, 1=almost none, 2=minor, 3severe)										
	Removal Rate		1st stage		2nd stage		3rd stage		4th stage	
	Process	Rate (A/min)	Time	Peeling	Time	peeling	Time	peeling	Time	peeling
Split1	RR=3.4/PI=120/H=10	4000	60	1	30	2	30	2.5	Stop	–
Split2	RR=3.4/PI=10/H=120	1200	60	0	180	0	180	0	180	0
Split3	RR=6.8/pi=120/H=10	5700	60	0.5	30	0.5	30	0.5	Stop	–
Split4	RR=6.8/PI=10/H=120	1100	60	0.5	180	0.5	180	1	180	1

IN THE DRAWINGS:

Applicant proposes amending the drawings as shown in a separate request for correction of the drawings. Figure 1 has been amended to include a (PRIOR ART) designation. Figure 2 has been amended to remove erroneously included matter as indicated in red ink. Figure 3 has been amended to correct the reference numeral of the substrate as 110.

IN THE CLAIMS:

Please cancel claims 6, 29, 33, and 34 without prejudice, and amend the claims as follows:

1. (Amended) A method for processing a substrate, comprising:

positioning a substrate having a conductive material formed thereon in a polishing apparatus having one or more rotational carrier heads and one or more rotatable platens, wherein the carrier head comprises a retaining ring and a membrane for securing a substrate in the carrier head and the platen has a polishing article disposed thereon;

contacting the substrate surface with the polishing article at a ratio of retaining ring contact pressure to membrane pressure of greater than about 1.1:1; and